ABSTRACT OF THE DISCLOSURE

A photosensitive film pattern formed through only one photolithography step and having difference in film thickness is formed utilizing difference in amount of light emitted to the photosensitive film on a film to be etched, and the film to be etched is etched two times to form plural patterns therein by utilizing the difference in film thickness of the photosensitive film pattern, thereby reducing the number of whole manufacturing process steps. In this case, at the time of etching and removing thin photosensitive film out of the photosensitive film pattern, the upper layer of thick photosensitive film out of the photosensitive film pattern has already been modified to a silica film nearly free from being affected by dry-etching, and therefore, the thick photosensitive film can maintain its planar shape nearly equal to that of the thick photosensitive film before etching the thin photosensitive film. Accordingly, the film to be etched is etched to have a pattern nearly equal to designed pattern by using the silica film as a mask.

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